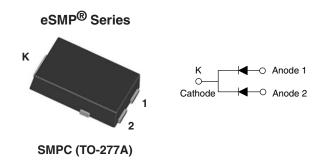
Vishay Semiconductors

Hyperfast Rectifier, 2 x 2 A FRED Pt®



www.vishay.com

LINKS TO ADDITIONAL RESOURCES



PRIMARY CHARACTERISTICS				
I _{F(AV)}	2 x 2 A			
V _R	200 V			
V _F at I _F	0.75 V			
t _{rr (typ.)}	24 ns			
T _J max.	175 °C			
Package	SMPC (TO-277A)			
Circuit configuration	Common cathode			

FEATURES

- Hyperfast recovery time, reduced $\mathsf{Q}_{\mathrm{rr}},$ and soft recovery
- 175 °C maximum operating junction temperature
- Specified for output and snubber operation
- Low forward voltage drop
- · Low leakage current
- Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C
- AEC-Q101 qualified, meets JESD 201 class 2 whisker test
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION / APPLICATIONS

State of the art hyperfast recovery rectifiers specifically designed with optimized performance of forward voltage drop and hyperfast recovery time.

The planar structure and the platinum doped life time control guarantee the best overall performance, ruggedness, and reliability characteristics.

These devices are intended for use in snubber, boost, lighting, piezo-injection, as high frequency rectifiers, and freewheeling diodes.

The extremely optimized stored charge and low recovery current minimize the switching losses and reduce power dissipation in the switching element.

MECHANICAL DATA

Case: SMPC (TO-277A)

Molding compound meets UL 94 V-0 flammability rating Halogen-free, RoHS compliant

Terminals: matte tin plated leads, solderable per J-STD-002

ABSOLUTE MAXIMUM RATINGS					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
Peak repetitive reverse voltage		V _{RRM}		200	V
Average rectified forward current	per device	I	T _{Sp} = 165 °C	4	
Average rectilled forward current	per diode	IF(AV)		2	А
Non-repetitive peak surge current	per device		T,I = 25 °C	90	A
Non-repetitive peak surge current	per diode	IFSM	1J = 25°C	50	
Operating junction and storage terr	nperatures	T _J , T _{Stg}		-65 to +175	۵°

ELECTRICAL SPECIFICATIONS ($T_J = 25 \text{ °C}$ unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Breakdown voltage, blocking voltage	V_{BR}, V_{R}	I _R = 100 μA	200	-	-	
Forward voltage, per diode	VF	I _F = 2 A	-	0.88	0.95	V
Forward voltage, per diode	۷F	I _F = 2 A, T _J = 125 °C	-	0.75	0.82	
Reverse leakage current, per diode	1	$V_{R} = V_{R}$ rated	-	-	2	
Reverse leakage current, per diode	I _R	$T_J = 125 \text{ °C}, V_R = V_R \text{ rated}$	-	1	8	μA
Junction capacitance	CT	V _R = 200 V	-	8	-	pF

Revision: 13-Jan-2021

1

Document Number: 94973

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>



HALOGEN

FREE



www.vishay.com

Vishay Semiconductors

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
		$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t =$	= 50 A/µs, V _R = 30 V	-	24	-	
Powerse receivery time	+	$I_{\rm F} = 0.5 \text{ A}, I_{\rm R} = 1 \text{ A}$	A, I _{rr} = 0.25 A	-	-	25	ns
Reverse recovery time	t _{rr}	T _J = 25 °C		-	16	-	
		T _J = 125 °C		-	22	-	
Peak recovery current	I _{RRM}	T _J = 25 °C	I _F = 2 A dI _F /dt = 200 A/µs V _R = 160 V	-	2	-	
Peak recovery current		T _J = 125 °C		-	3	-	A
	Q _{rr}	T _J = 25 °C]	-	16	-	nC
neverse recovery charge	Reverse recovery charge Q _{rr}	T _J = 125 °C		-	30	-	lic

THERMAL - MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS	
Maximum junction and storage temperature range	T _J , T _{Stg}		-65	-	175	°C	
Thermal resistance, junction to mount, per diode	R _{thJM}		-	4.5	5.5	°C/W	
Approximate weight				0.1		g	
				0.0035		oz.	
Marking device		Case style SMPC (TO-277A)		JC	H2		



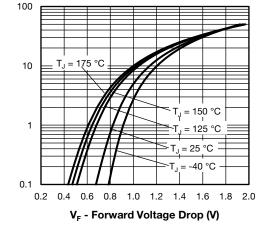


Fig. 1 - Typical Forward Voltage Drop Characteristics

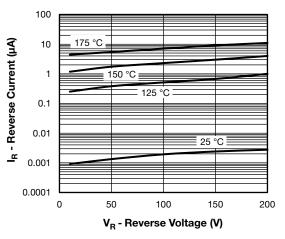
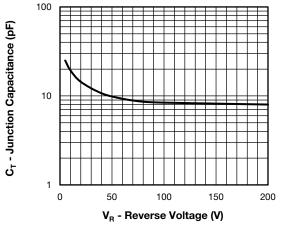


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage



Vishay Semiconductors



www.vishay.com

Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

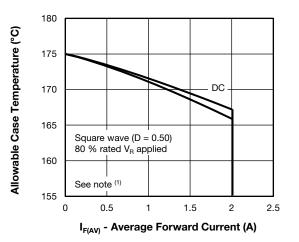


Fig. 4 - Maximum Allowable Case Temperature vs. Average Forward Current

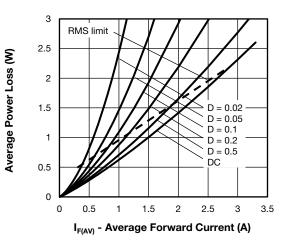


Fig. 5 - Forward Power Loss Characteristics

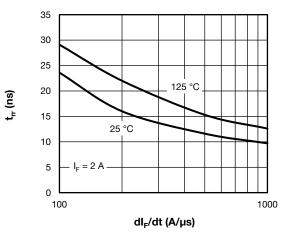


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

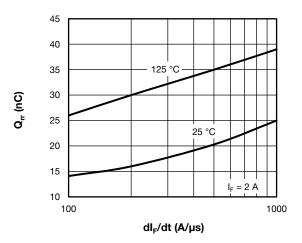


Fig. 7 - Typical Stored Charge vs. dl_F/dt

Note

⁽¹⁾ Formula used: $T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}$;

 $\begin{array}{l} \mathsf{Pd} = \mathsf{forward} \ \mathsf{power} \ \mathsf{loss} = \mathsf{I}_{\mathsf{F}(\mathsf{AV})} \times \mathsf{V}_{\mathsf{FM}} \ \mathsf{at} \ (\mathsf{I}_{\mathsf{F}(\mathsf{AV})}/\mathsf{D}) \ (\mathsf{see} \ \mathsf{fig.} \ \mathsf{5}); \\ \mathsf{Pd}_{\mathsf{REV}} = \mathsf{inverse} \ \mathsf{power} \ \mathsf{loss} = \mathsf{V}_{\mathsf{R1}} \times \mathsf{I}_{\mathsf{R}} \ (1 - \mathsf{D}); \ \mathsf{I}_{\mathsf{R}} \ \mathsf{at} \ \mathsf{V}_{\mathsf{R1}} = \mathsf{rated} \ \mathsf{V}_{\mathsf{R}} \end{array}$

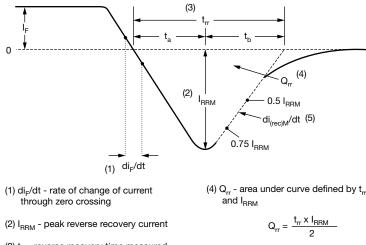
Revision: 13-Jan-2021

3

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

VS-4CSH02HM3

Vishay Semiconductors



(3) t_{rr} - reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 8 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

SHAY

www.vishay.com

S- 4	с	S	н	02	н	М3	
1) (2)	3	4	5	6	7	8	I
	hay Serr rrent ratii		-	oduct			
	cuit confi commo	-					
	SMPC						
 Process type, H = hyper fast recovery 							
- Voltage code (02 = 200 V)							
- H=	H = AEC-Q101 qualified						
- M3	= haloge	en-free,	RoHS-0	complia	nt, and	terminat	tions lead (Pb)-

ORDERING INFORMATION (Example)							
PREFERRED P/N	QUANTITY PER REEL	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION				
VS-4CSH02HM3/86A	1500	1500	7" diameter plastic tape and reel				
VS-4CSH02HM3/87A	6500	6500	13" diameter plastic tape and reel				

LINKS TO RELATED DOCUMENTS				
Dimensions www.vishay.com/doc?95570				
Part marking information	www.vishay.com/doc?95565			
Packaging information	www.vishay.com/doc?88869			

Revision: 13-Jan-2021

Document Number: 94973

For technical questions within your region: <u>DiodesAmericas@vishay.com</u>, <u>DiodesAsia@vishay.com</u>, <u>DiodesEurope@vishay.com</u> THIS DOCUMENT IS SUBJECT TO CHANGE WITHOUT NOTICE. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT <u>www.vishay.com/doc?91000</u>

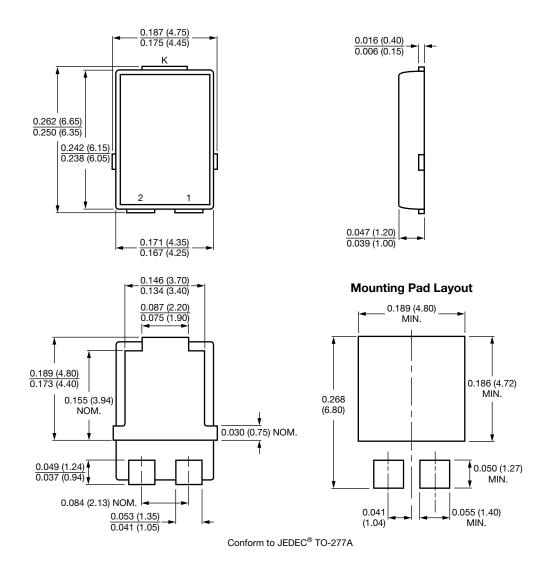
Outline Dimensions





SMPC (TO-277A)

DIMENSIONS in inches (millimeters)





Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Vishay products are not designed for use in life-saving or life-sustaining applications or any application in which the failure of the Vishay product could result in personal injury or death unless specifically qualified in writing by Vishay. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

© 2025 VISHAY INTERTECHNOLOGY, INC. ALL RIGHTS RESERVED

Revision: 01-Jan-2025

1